

ABSTRACT OF THE DISCLOSURE

This surface emitting semiconductor device 1 comprises a first conductivity type semiconductor region, an active layer, a second conductivity type semiconductor layer and current block semiconductor region. The first conductivity type semiconductor region is provided on a surface made of GaAs semiconductor. The active layer is provided on the first conductivity type semiconductor region. The active layer has a side surface. The second conductivity type semiconductor layer is provided on the active layer. The second conductivity type semiconductor layer has a side surface. The current block semiconductor region is provided on the side surface of the active layer and on the side surface of the second conductivity type semiconductor layer. The active layer is made of III-V compound semiconductor including at least nitrogen element as a V group element.